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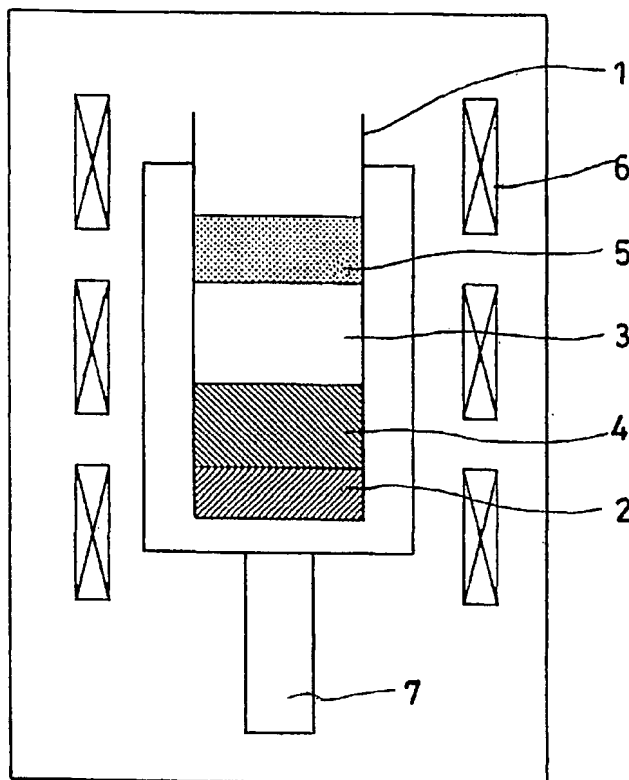
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- (71) Applicant (for all designated States except US): **SHOWA DENKO K.K.** [JP/JP]; 13-9, Shiba Daimon 1-chome, Minato-ku, Tokyo 105-8518 (JP).
- (72) Inventor; and
(75) Inventor/Applicant (for US only): **MATSUMOTO, Fumio** [JP/JP]; c/o SHOWA DENKO K.K., 1505, Shimokagemori, Chichibu-shi, Saitama 369-1871 (JP).
- (74) Agents: **FUKUDA, Kenzo** et al.; Kashiwaya Building, 6-13, Nishishinbashi 1-chome, Minato-ku, Tokyo 105-0003 (JP).
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(54) Title: InP SINGLE CRYSTAL, GaAs SINGLE CRYSTAL, AND METHOD FOR PRODUCTION THEREOF



(57) Abstract: A method for the production of an InP single crystal includes gradually cooling a molten raw material held in contact with a seed crystal to solidify the molten raw material from a lower part toward an upper part of an interior of a crucible and grow a single crystal, causing the seed crystal to possess an average dislocation density of less than 10000/cm² and assume substantially identical cross-sectional shape and size with a cross-sectional shape and size of a single crystal to be grown, and allowing the InP single crystal to be grown to retain a non-doped state or a state doped with Fe or Sn.

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